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Docket No.: ASA-481-10

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.: 7,115,344

Issue Date: October 3, 2006

Inventor:

N. HASEGAWA et al.

Title:

PHOTOMASK AND PATTERN FORMING METHOD EMPLOYING

THE SAME

Customer No.:

24956

REQUEST FOR CERTIFICATE OF CORRECTION APPLICANTS' MISTAKE (37 CFR §1.323)

Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

or Corection Enclosed is a completed Certificate of Correction form. Please issue a Certificate of Correction for the underscored material. The Certificate of Correction is necessary to clarify an expression in each of claims 1 and 8 wherein, due to an inadvertent error that occurred during preparation of the claims, the expression pattern formed on said element forming area was inaccurately set forth in claims 1 and 8 as "pattern formed element forming area." It is noted that the expression is accurately set forth in claim 15.

No new matter is added by the proposed correction, which is believed to be a mistake of minor character, indeed of a clerical or typographical nature. Further, no re-examination is required. Therefore, it is believed that the requirements of 35 U.S.C. §255 are met.

> 10/04/2006 SDENBOB1 00000121 7115344 109.00 OP 01 FC:1811

Since the Certificate of Correction is necessitated by an error on the part of the Applicants, in accordance with 37 CFR §1.20(a) our Credit Card Payment Form in the amount of \$100.00 is attached in payment of the appropriate fee.

The Commissioner is hereby authorized to charge additional payment due or to credit any overpayment, to Deposit Account no. 50-1417.

Respectfully submitted,

MATTINGLY, STANGER, MALUR & BRUNDIDGE, P.C.

y wew

Daniel J. Stanger / Registration No. 32,846

(703) 684-1120

PTO/SB/44 (04-05)
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(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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PATENT NO.:

7,115,344

APPLICATION NO.:

10/777,060

ISSUE DATE:

October 3, 2006

INVENTOR(S):

N. HASEGAWA et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Claims

Please amend claims 1 and 8 as follows:

1. A method of manufacturing a semiconductor device, comprising the steps of: preparing a phase shifting mask including (a) an element forming area having a semitransparent phase shifting film, and (b) a light shielding area provided at a peripheral edge of said element forming area and serving to make an intensity of light having passed through said light shielding area smaller than an intensity of light having passed through said semitransparent phase shifting film, as measured on a to-be-exposed photoresist film, and said light shielding area further including a target pattern for mask aligning; and

transmitting, with a projection exposure optical system, a pattern formed <u>on said</u> element forming area of said phase shifting mask onto said photoresist film.

8. A method of manufacturing a semiconductor device, comprising the steps of: preparing a phase shifting mask including (a) an element forming area having a first semitransparent phase shifting film having a transmittance with respect to exposure light not higher than 25%, and (b) a light shielding area provided at a peripheral edge of said element forming area and serving to make an intensity of light having passed through said light shielding area smaller than an intensity of light having passed through said semitransparent phase shifting film, as measured on a to-be-exposed photoresist film, and said light shielding area further including a target pattern for mask aligning;

preparing a semiconductor substrate at which said photoresist film to be exposed is formed; and transmitting, with a projection exposure optical system, a pattern formed on said element forming area of said phase shifting mask onto said photoresist film.

MAILING ADDRESS OF SENDER
Daniel J. Stanger
MATTINGLY, STANGER, MALUR & BRUNDIDGE, P.C.
1800 Diagonal Road, Suite 370
Alexandria, Virginia 22314

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Patent

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